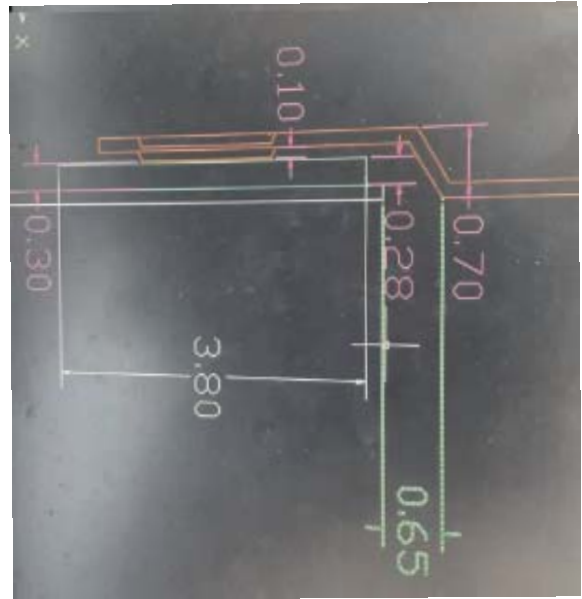
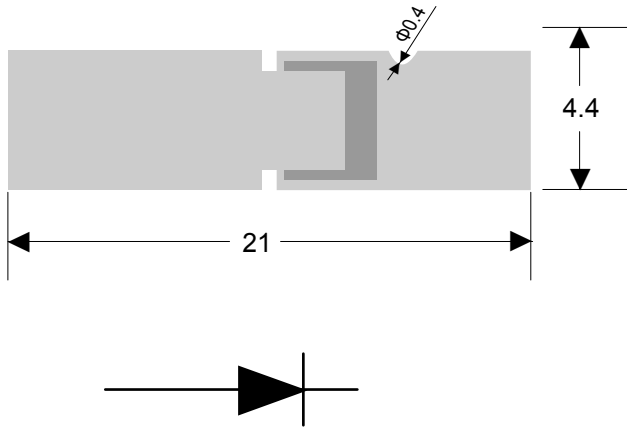


STRUCTURE:



CHIP SIZE : 120mil

UNIT : mm

SPECIFICATION

Characteristic	Symbols	SBR12A45V	Unit
最大峰值反向电压 Maximum repetitive peak reverse voltage	V_{RRM}	45	V
最大正向平均整流电流 Maximum average forward rectified current	I_{FM}	12	A
正向峰值浪涌电流 8.3ms单一正弦半波 Peak forward surge current 8.3 ms single half sine-wave	I_{FSM}	200	A
典型热阻 Typical thermal resistance	$R_{\theta JA}$	66	$^{\circ}C/W$
工作温度 Operating Temperature Range	$V_R \leq 80\% V_{RRM}$	T_J	-65 to +150
	DC Forward Mode	T_J	≤ 200
存储温度 Storage Temperature Range	T_{STG}	-65 to +175	$^{\circ}C$
最大正向电压降 @ $I_F = 12A$ Forward Voltage Drop	V_F	0.49	V
最大反向漏电流 Leakage Current	I_R	0.12	mA